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و بحث های درسی:

• Stability of the solid/liquid interface

• Faceted/non-faceted interfaces

• Faceted/non-faceted interfaces

• Growth and coarsening of solid particles

• Effects of fluid flow on solidification structure

• Solute redistribution

• Directional solidification

• Eutectic solidification

• Grain refinement

• Macro- and micro-segregation

Semi-solid processing of alloys

• Effect of pressure on solidification structure

Rapid solidification

Solidification of composites

Heat transfer in solidification

Inclusion and porosity formation during solidification

...

TABLE 1.1

THE CHANGE IN VOLUME ON MELTING OF SOME COMMON METALS⁴

Metal	Crystal structure	Melting point	Change in volume on melting (%)
Aluminium	f.c.c.	660	+6.0
Gold	f.c.c.	1 063	+5.1
Zinc	h.c.p.	420	+4.2
Copper	f.c.c.	1 083	+4.15
Magnesium	h.c.p.	650	+4.1
Cadmium	h.c.p.	321	+4.0
Iron	b.c.c./f.c.c.	1 537	+3.0
Tin	tetr.	232	+2.3
Antimony	rhombohedral	631	-0.95
Gallium	f.c. orthorhombic	30	-3.2
Bismuth	rhombohedral	. 271	-3.35
Germanium	dia. cubic	937	-5.0

⁴ Data from Schneider and Heymer. ¹

TABLE 1.2

		COMM	ON METAL	Sa		
Metal	Crystal structure	Melting point (°C)	Latent heatb of melting (L _m)	Boiling point (°C)	Latent heat ^b of vaporisation (L _b)	$\frac{L_{\rm b}}{L_{\rm m}}$
Aluminium	f.c.c.	660	2.5	2 480	69.6	27-8
Gold	f.c.c.	1 063	3.06	2 950	81.8	26.7
Copper	f.c.c.	1 083	3.11	2 575	72.8	23.4
Iron	f.c.c./b.c.c.	1 536	3.63	3 070	81.3	22.4
Zinc	h.c.p.	420	1.72	907	27.5	16.0
Cadmium	h.c.p.	321	1.53	765	23.8	15.6
Magnesium	h.c.p.	650	2.08	1 103	32.0	15.4

^a Data from Smithells.²
^b Latent heats in kcal mol -1.

TABLE 1.4 COMPARISON OF STRUCTURAL DATA FOR LIQUID AND SOLID METALS

	Li	quid	Solid		
Metal	atomic separation	co-ordination number	atomic separation	co-ordination number	
Aluminium Zinc	2.96	10-11	2.86	12	
Zinc	2.94	11	2.65	6	
C 1 .			2.94	6	
Cadmium	3-06	8	2.97	6	
_			3.30	6	
Gold	2.86	11	2.88	12	

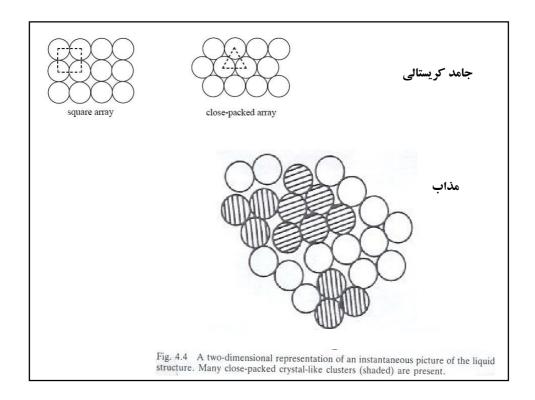
⁴ Data abstracted from Vineyard.⁵

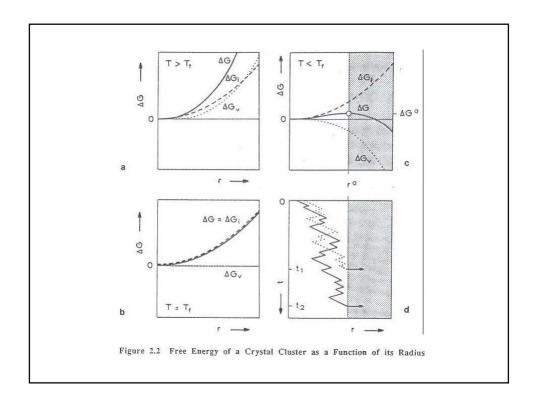
TABLE 1.3 ENTROPY CHANGES DURING THE HEATING OF SOME COMMON METALS

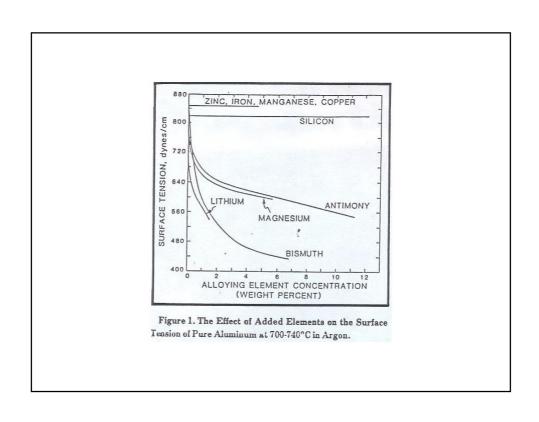
Metal	Change in entropy ^b $298^{\circ}K$ to melting point ΔS	Entropy of melting $\Delta S_{\rm m}$	$\frac{\Delta S_{\rm m}}{\Delta S}$
Cadmium	4.53	2.46	0.54
Zinc	5.45	2.55	0.47
Aluminium —	7.51	2.75	0.37
Magnesium	7.54	2.32	
Copper	9.79		0.31
Gold	9.78	2.30	0.24
Iron	15.50	2·21 2·00	0·23 0·13

مايع	جامد و ،	هـس	خراص	: مقایسه	جذول٦-١

خواص	جامد	مايع
زن مخصوص در دمای فوب (gt/cm ^۳)	۸/۲۲	V/9T
اماه بین انعی یا گمترین فاصله بین انمها در دمای ذرب (A^)	1/14	Y/AA
نسریب مقاومت الکتریکی در دمای ذویهٔ (μΩ-cm)	11	77
شریب تفوذ در دمای ذوب (cm ^۲ /sec)	14	1 = -0
شاخص سياليت	مدول برشي	گرانروی



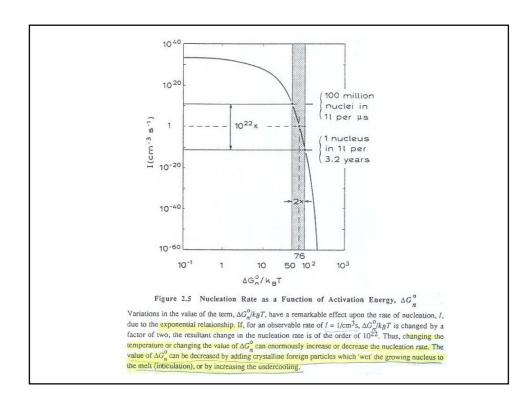


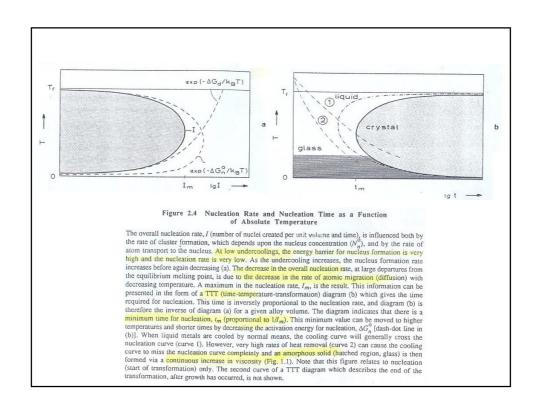


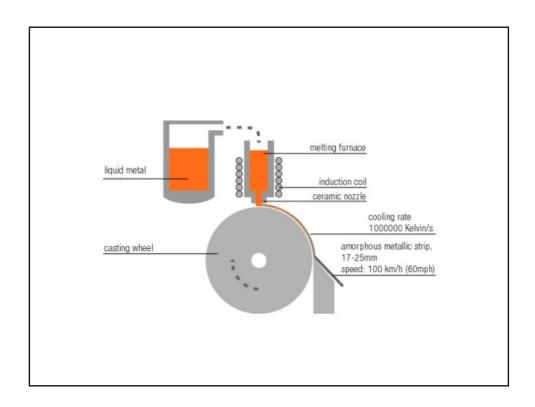
	~					
Material	Melting point (K)	under	mum† cooling (C)	Material	Melting point (K)	Maximum undercooling △T (C)
		Large samples	Small†† samples		Westerland of the Control of the Con	Small samples
Ag	1234	30	227	H₂O	273	39
Al	932		130	NH ₃	195.5	40
Au	1336		221	BF ₃	144.5	17.8
Bi	544	30	90	SO ₂	197.6	33
Co	1763		330	CH ₃ Cl	175.6	55.6
Cu	1356		236	CCl ₄	250	50.4
Ga	302.8	55	76	CBr ₄	363	82
Ge	1231	30	193	C ₆ H ₆	278	70 66.5
Fe	1803	100	. 295	(CH ₂ Br) ₂	282	120
Hg	234.1	14	46	C6H3COOH	395	24.4
Mn	1493		308	CH ₃ Br	179.4	35.7
Ni	1725		319	CH ₃ NH ₂	179.7 209.7	52.5
P	317	115	80	CHCl ₃	- 344	86
Pb	600.7		80	Diphenyl	353	94.4
Pd	1828		332 370	Naphthalene Cyclopropane	145.8	17.8
Pt	2046	70	165	Thiophene	234.9	50.7
S	393	70	135	InSb	698	110
Sb	903		25	InSb+1% Te	690	55
Se Sn	493 505	31	115	1113071/016	0,0	23

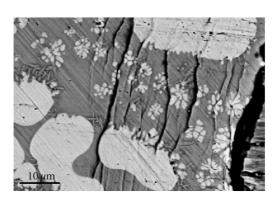
† Note that Burns and Turnbull (1966) have shown that the undercooling achieved depends on the rate of cooling. †† The idea of using small samples is to reduce the chance of nucleation by a foreign solid particle. However, results on very small samples should be treated with care. Petrov (1965) has shown that samples of lead, bismuth and antimony with diameters of about 2.5×10^{-5} mm had melting points which differed from those found in the bulk by +53, -39 and -15 C respectively.

Type of melt	Range		Median		
	4T/T	$\gamma_{\rm LS}~({\rm erg~cm^{-2}})$	$\Delta T/T$	γ _{LS} (erg cm ⁻²)	
Metals	0.13-0.32	32-260	0.19	130	
	0.14-0.24	40-180	0.18	65	
Molecular	0.12-0.32	7-35	0.21	24	
Long chain					
hydrocarbons	0.037-0.043	7-10	0.041	9	
Polymers	0.13-0.22		0.18	~20	









SEM micrograph of a particle-reinforced ex situ metallic glass matrix composite exhibiting shear band arresting.

Smaller dendrites and needle crystal phase are also present.

D. C. Hofmann, Journal of Materials, 2013, Article ID 517904.

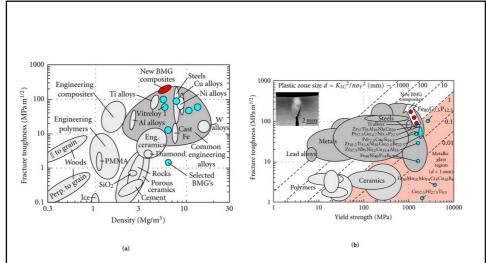
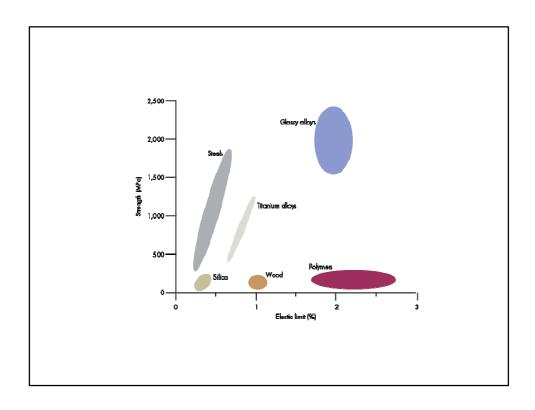


Figure 7: (a) Ashby map of fracture toughness versus density showing the location of select bulk metallic glasses and Zr-Ti-Nb-Cu-Be bulk metallic glass matrix composites. The composite alloys have among the highest fracture toughness for their density. (b) Ashby map of fracture toughness versus yield strength showing select metallic glasses and composites. Contour lines indicate plastic zone size and the shaded region signifies the d < 1 mm region that typically confines monolithic metallic glasses. The plastic zone size of the toughness composites is shown in the inset.



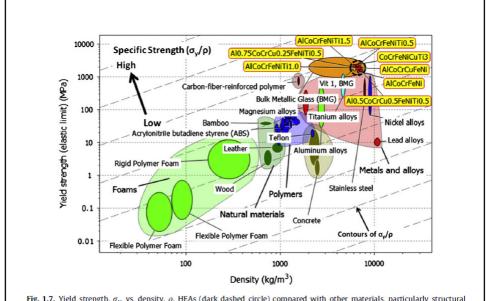
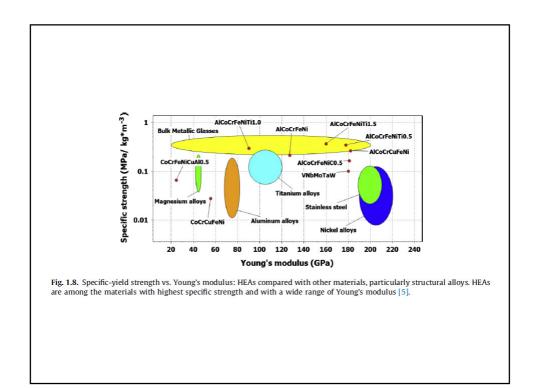
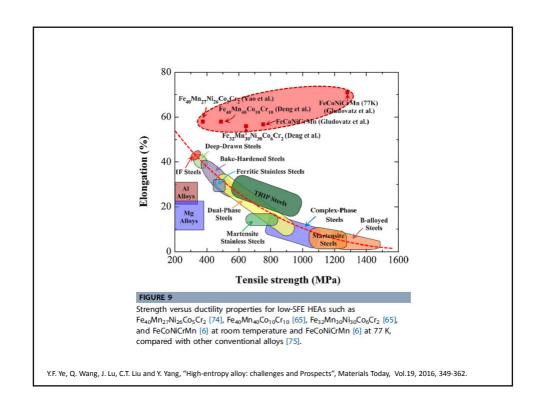


Fig. 1.7. Yield strength, σ_y , vs. density, ρ . HEAs (dark dashed circle) compared with other materials, particularly structural alloys. Grey dashed contours (arrow indication) label the specific strength, $\sigma_y | \rho$, from low (right bottom) to high (left top). HEAs are among the materials with highest strength and specific strength [5].





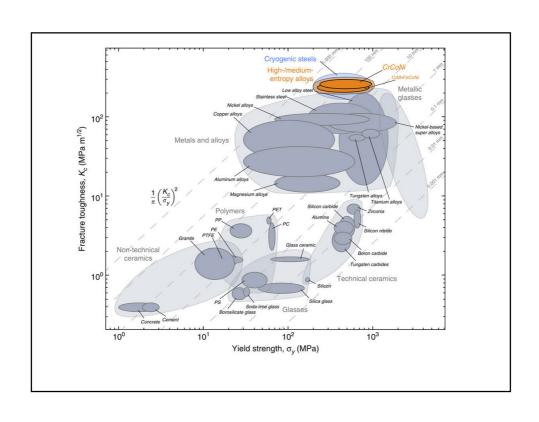


Table 2.1 Critical Dimensions and Activation Energy for the Nucleation of a Spherical Nucleus in a Pure Melt $(\Delta g = \Delta s_f \Delta T)$

	Homogeneous Nucleation	Heterogeneous Nucleation
r°	$-\frac{2\sigma}{\Delta g}$	$-\frac{2\sigma}{\Delta g}$
n°	$-\left(\frac{32\pi}{3\nu'}\right)\left(\frac{\sigma}{\Delta g}\right)^3$	$-\left(\frac{32\pi}{3v}\right)\left(\frac{\sigma}{\Delta g}\right)^3 f(\theta)$
ΔG_n^{0}	$\left(\frac{16\pi}{3}\right)\left(\frac{\sigma^3}{\Delta g^2}\right)$	$\left(\frac{16\pi}{3}\right)\left(\frac{\sigma^3}{\Delta g^2}\right)f(\theta)$

Table 2.2 Values of the Expression: $f(\theta) = (1/4)(2 + \cos\theta)(1 - \cos\theta)^2$

θ (°)	Type of Nucleation	$f(\theta)$
0 complete wetting	no nucleation barrier #)	0
10 \		/ 0.00017
20		0.0027
30		0.013
40		0.038
50		0.084
70 >	heterogeneous	(0.25
90 (0.5
110		0.75
130		0.92
150		0.99
170 /		0.9998
180 no wetting	homogeneous	1

#) immediate growth can occur

TABLE 2.2

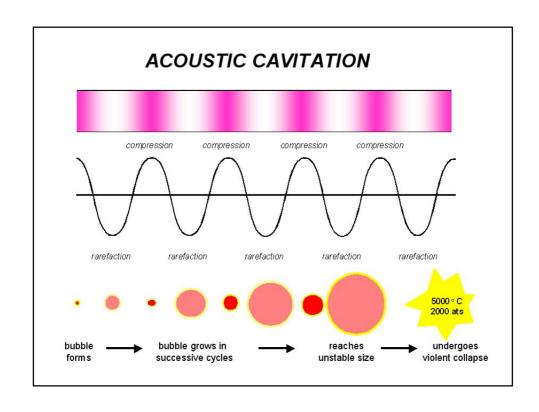
COMPOUNDS USED TO NIUDY THE HETEROGENEOUS NUCLEATION OF ALUMINIUM FROM ITS MELT⁴

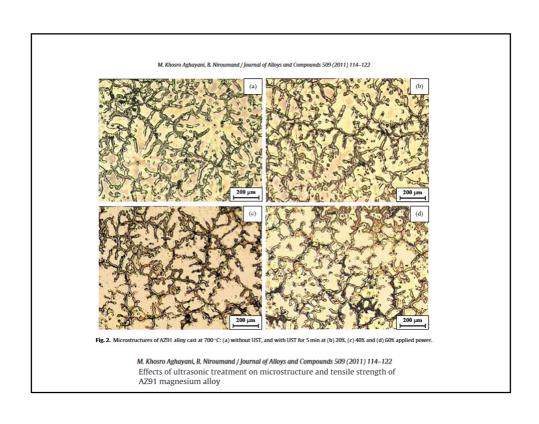
Compound	Crystal structure	δ for close-packed planes	Nucleating effect
VC	Cubic	0.014	Strong
TiC	Cubic	0.060	Strong
TiB ₂	Hexagonal	0.048	Strong
AlB ₂	Hexagonal	0.038	Strong
ZrC	Cubic	0.145	Strong
NhC	Cubic	0.086	Strong
W_2C	Hexagonal	0.035	Strong
Cr_3C_2	Complex	· man	Weak or nil
Mn3C	Complex	Ma (c)	Weak or nil
Fe ₃ C	Complex	***	Weak or nil

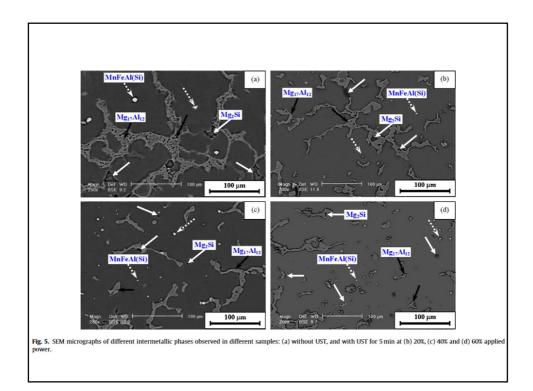
	TABLE 6.1
SOM	GRAIN REFINING NUCLEANTS

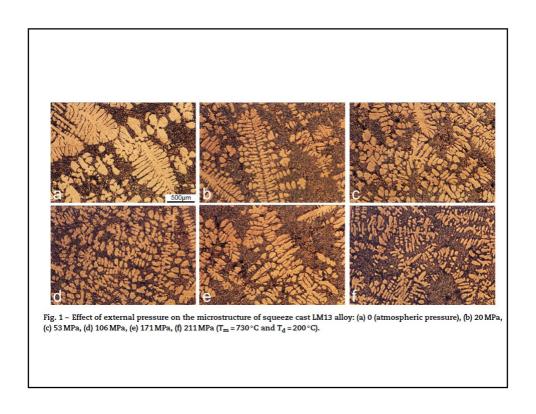
Metal or alloy	Grain refiner	Comments
Magnesium and Mg-Zr		Zr or Zr-enriched Mg
alloys	alloy or salts	peritectic nuclei
Magnesium-aluminium	Carbon, for example as hexachlorethane	Al ₄ C ₃ or AlNAl ₄ C ₃ nuclei
Magnesium-aluminium	Superheating .	In presence of C,
	1 - 6	Al ₄ C ₃ and/or Al-Mn nuclei
Magnesium-aluminium- manganese	FeCl ₃	Fe-Al-Mn or Al ₄ C ₃ nuclei
Mg–Zn	FeCl ₃ or Zn-Fe	Fe compound nuclei
Mg–Zn	NH ₃	Nucleated by H2 (?)
Al alloys	Ti as reducible halide	TiC nucleus or peri-
	salts or as Al-Ti	tectic TiAl ₃
	hardener	The state of
Al alloys	Ti + B as reducible	TiB2 nuclei, more
•	halide salts or as	resistant to melt
	Al-Ti-B hardener	history
Al alloys	Boron as reducible	AlB ₂ nuclei
	halide salts or Al-B	
Al alloys	Niobium	

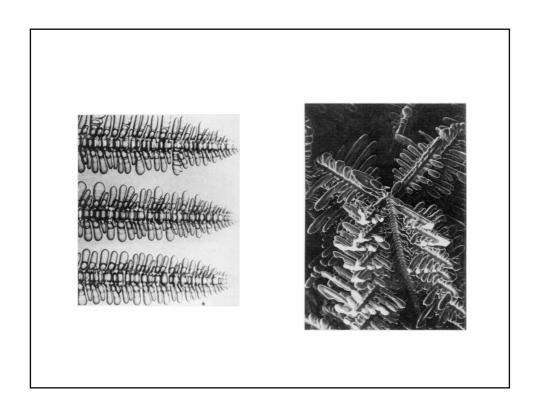
Cu alloys	Fe metal or alloy	Fe-rich peritectic nuclei
Bronzes	Transition nitrides and borides or FeB	lidelei
Cu-Al ₂ Cu eutectic Cu-7%Al Cu-9%Al	Titanium Mo, Nb, W, V Bi	Nucleates primary Al
Low alloy steel Low alloy steel	Titanium Transition elements and	
Silicon steel	carbides TiB ₂	Dissolves and precipi- tates TiN or TiC
Low alloy steel	Fe powder	Introduction of micro- chilling particles
Austenitic steel Tin alloys Lead alloys Lead alloys Type metal Monel	CaCN ₂ , nitrided Cr and other metallic powders Germanium or indium S Se, Te As, Te Lithium	In presence of increased nitrogen
Al-Si hypereutectic	Phosphorus as Cu-P, PNCl ₂ or proprietary inoculant	Refines primary Si
Fe-C (graphite) Fe-C-Si (graphite) Grey cast iron	Carbon	Refines eutectic, probably through nucleating graphite
Grey cast iron	Si alloys containing aluminium, alkaline earths and/or rare earths	Refines eutectic, may nucleate through precipitation of carbides or graphite

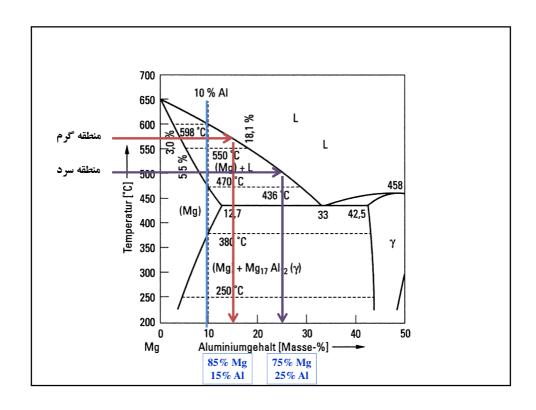


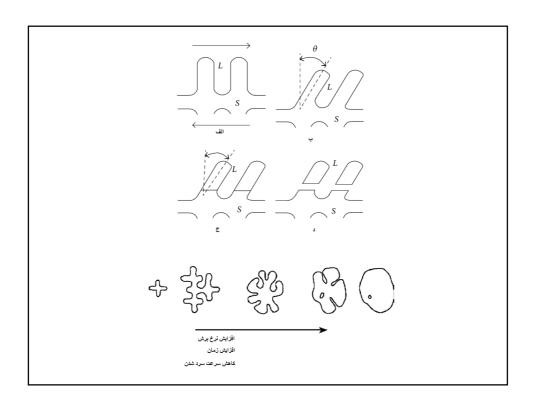


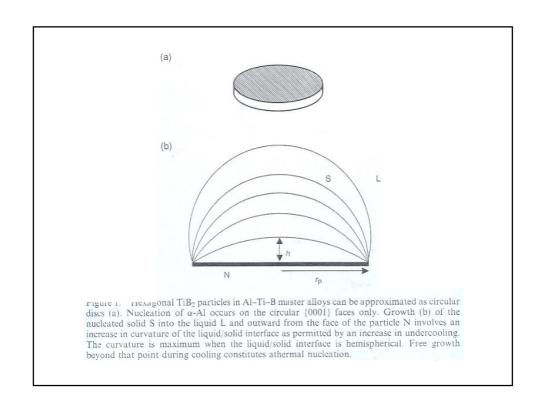












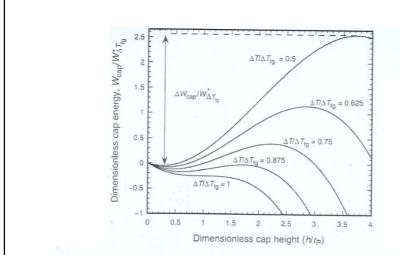
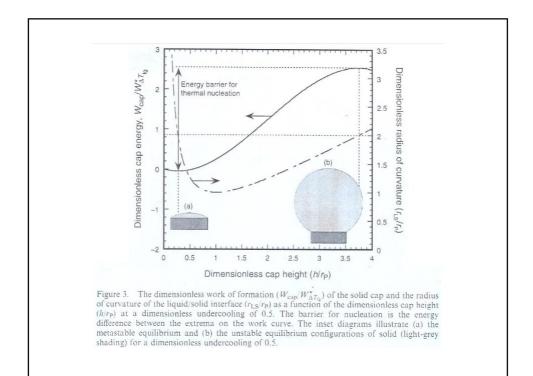
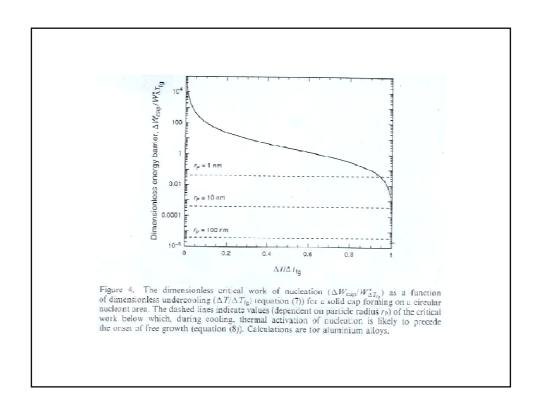
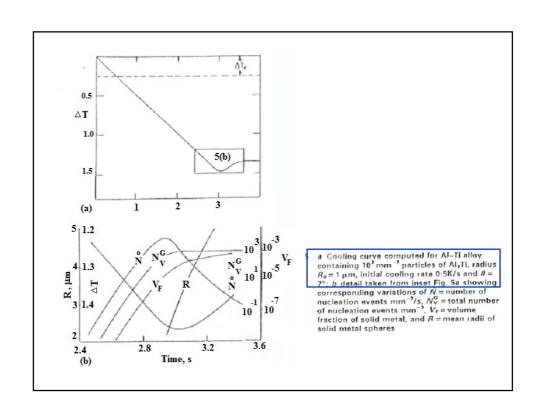
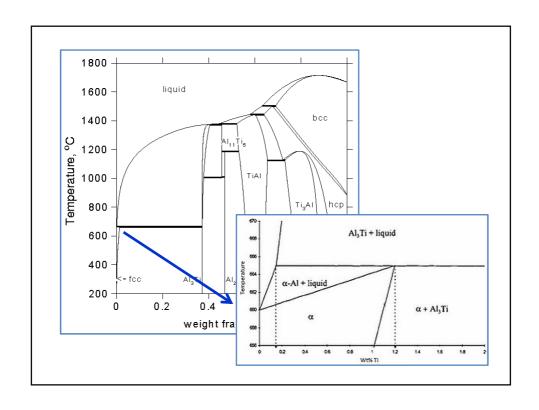


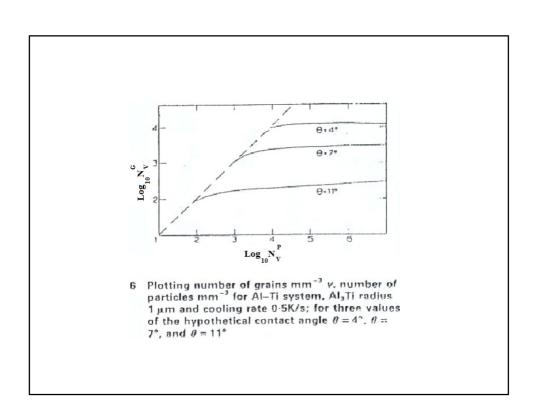
Figure 2. Dimensionless work of formation $(W_{\text{cup}}/W_{\Delta T_{\text{fg}}}^*)$ of solid cap on a circular nucleant area as a function of dimensionless cap height (h/r_{P}) for selected values of dimensionless undercooling $(\Delta T/\Delta T_{\text{fg}})$ (equation (5)). The minima (maxima) in these energy curves represent metastable (unstable) equilibrium configurations.

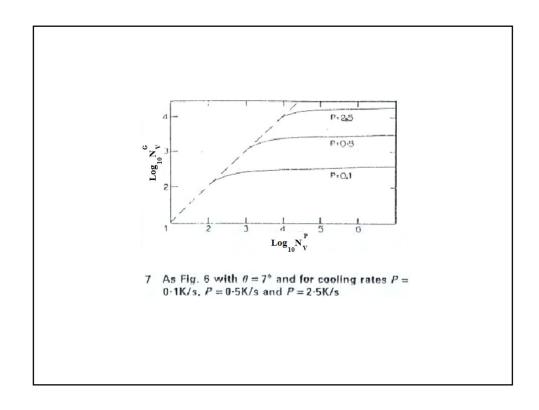


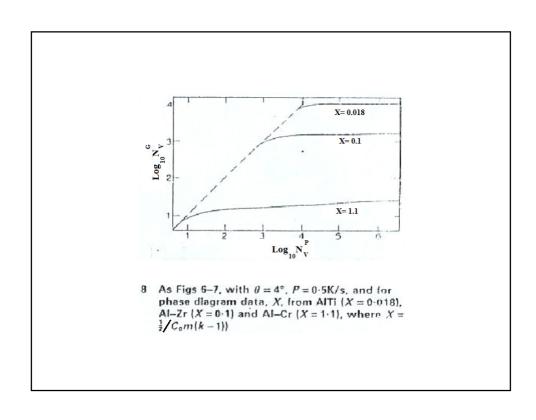


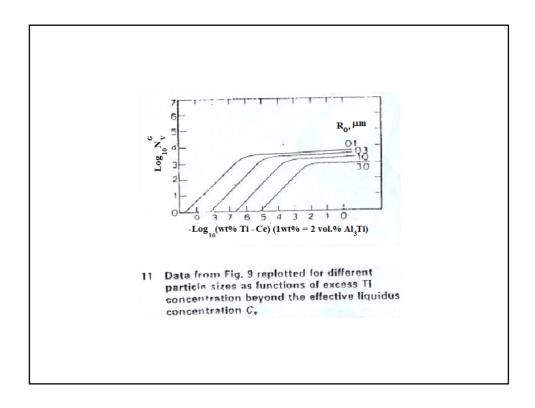


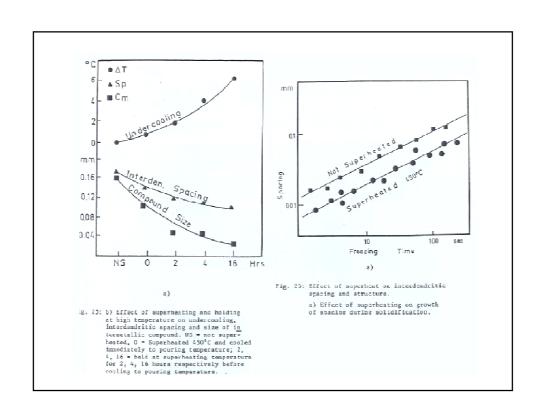


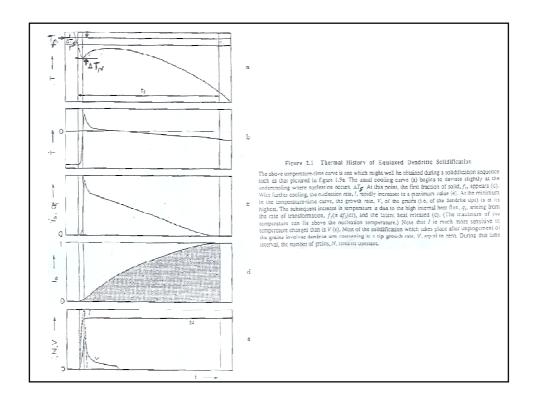


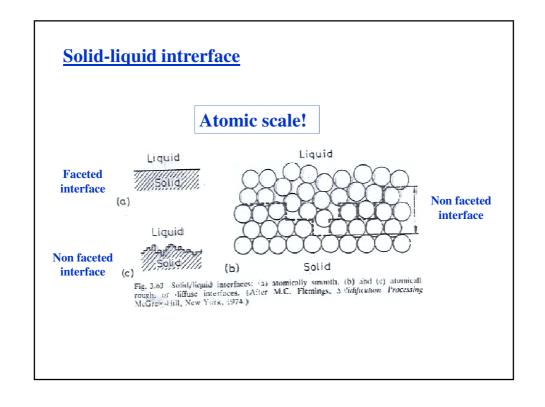


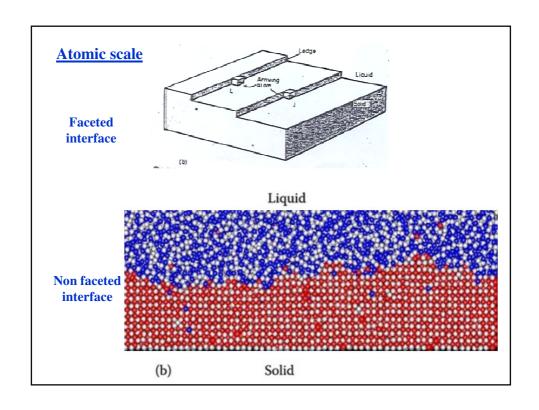


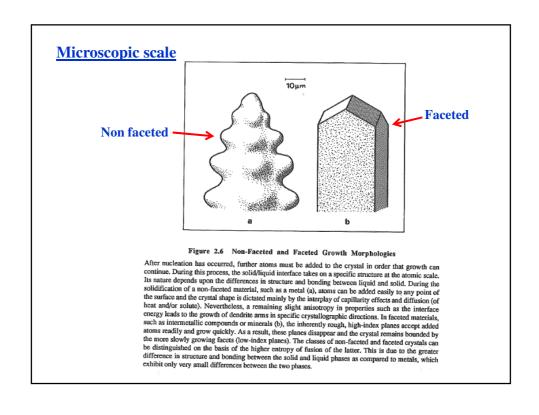






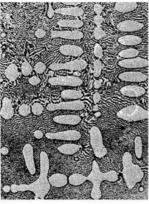


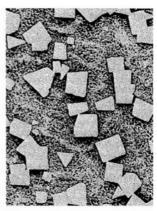




Microscopic scale

Cu-Ag 공정 기지내 Ag 수지상 Sn(Sb) 고용체 내에서 생성된 β'-SnSb 화합물

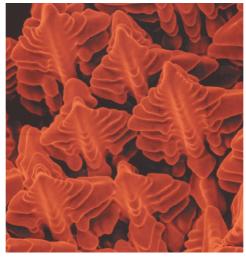




(a) Non-faceted

(b) Faceted

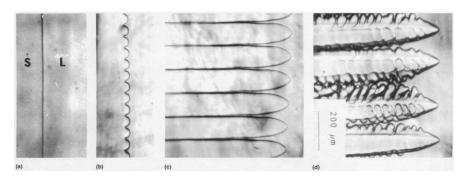
Examples of non-faceted growth morphologies



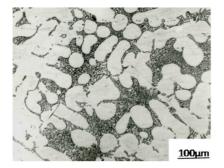
Non-faceted dendrites in a nickel-based super alloy single-crystal weld



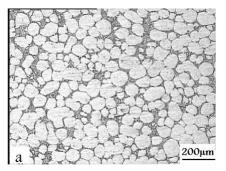




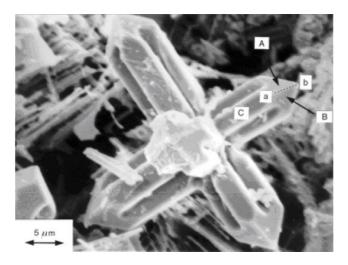
Non-faceted-interface morphology for SCN crystals



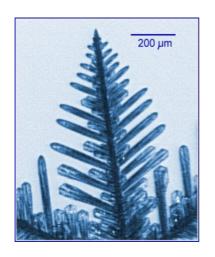
Non-faceted dendritic growth of a hypoeutectic Al-Si alloy



Non-faceted non-dendritic growth of a hypoeutectic Al-Si alloy

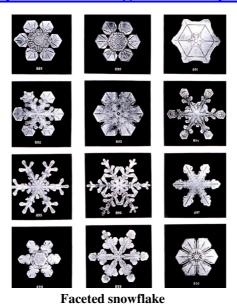


Faceted NbC dendrite in a Fe-34wt%Cr-5wt%Nb-4.5wt%C alloy

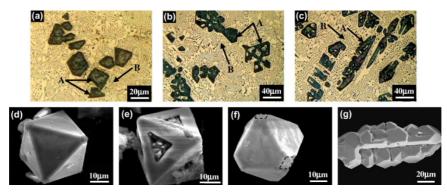




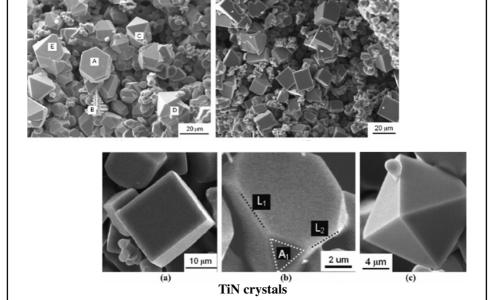
Faceted ice dendrite formation

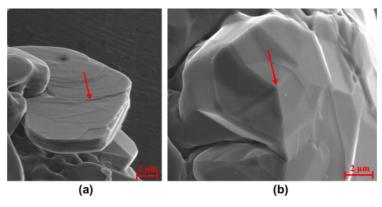


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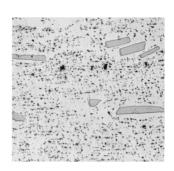
Faceted primary Mg₂Si particles in an Al–Si-Mg alloy

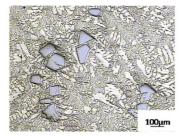




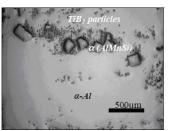
Faceted growth of graphite basal plane by
(a) 2-D nucleation and migration of ledges and
(b) spiral growth



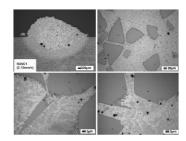




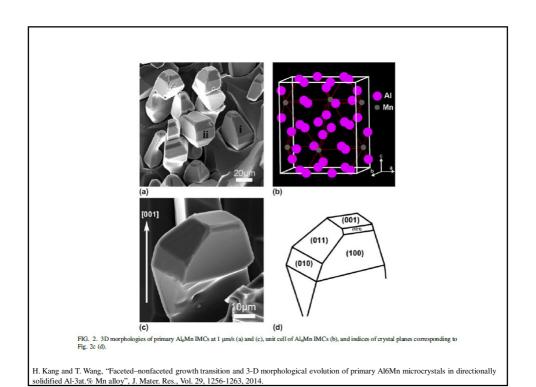
Faceted primary Si in an Al-Si alloy

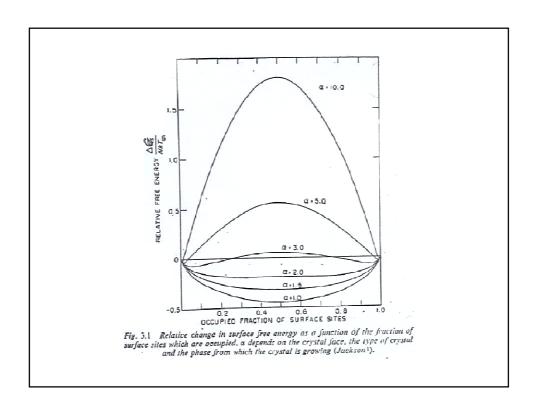


Faceted TiB₂ crystals in an Al alloy



NiWC in a laser surface alloyed sample





Faceted and Non-Faceted growth morphologies

Table 2.4 Growth Morphologies and Crystallisation Entropies

Dimensionless Entropy $(\Delta S_f/R)$	Supersaturated Substance	Phase	Morphology
~1	metals	melt	non-faceted
~1	'plastic' crystals	melt	non-faceted
2-3	semiconductors	solution	nf/faceted
2-3	semimetals	solution	nf/faceted
~6	molecular crystals	solution	faceted
~10	metals	vapour	faceted
~20	complex molecules	melt	faceted
~100	polymers	melt	faceted

Faceted and Non-Faceted growth morphologies

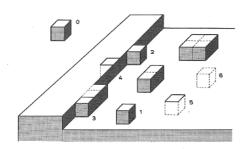


Figure 2.7 Variation in Bond Number at the Solid/Liquid Interface of a Simple-Cubic Crystal

of a Simple-Cubic Crystal

In order to understand the two types of growth shown in figure 2.6, the various ways in which an atom can be adsorbed at the solid/liquid interface have to be considered. Growth is determined by the probability that an atom will reach the interface and remain adsorbed there until it has been fully incorporated into the crystal. This probability increases with an increasing number of nearest neighbours in the crystal. The possible arrangements of atoms on the crystal interface are indicated here, where the numbers specify the number of seases with an increasing number of earest neighbours in the crystal (when the crystal coordination number is 6 as in a simple cubic crystal). The atoms of the liquid phase are not shown here. A special role is played by type 3 atoms in the growth of faceted crystals because, having three bonds, they can be considered to be situated half in the solid and half in the liquid. A likely growth sequence would be: addition of type 3 atoms until a row is complete; addition of a type 2 atom to start a new row; and so on until a layer is complete. Thereupon, nucleation of a new layer by the addition of a type 1 atom would be necessary. This is an unfavourable process and requires a very high undercooling. Therefore, other processes will play a role (Fig. 2.10).

Faceted and Non-Faceted growth morphologies

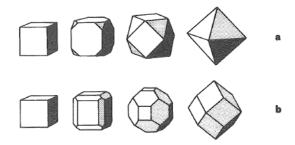
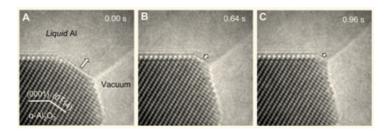


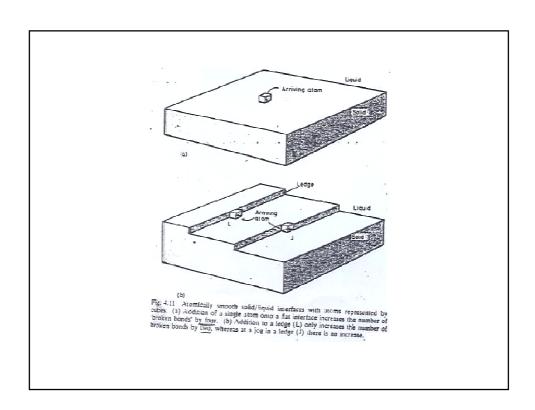
Figure 2.9 Development of Faceted Crystal Growth Morphologies

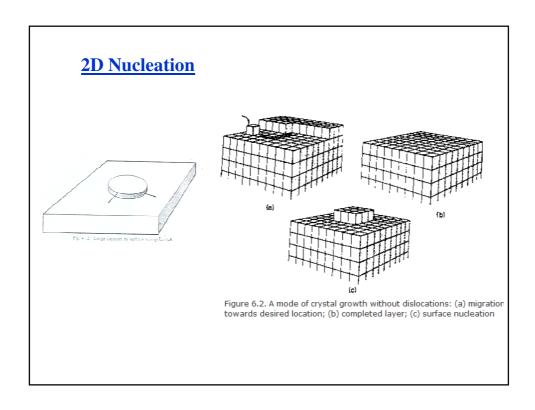
A growing cubic crystal which is originally bounded only by (100) planes (left hand side) will change its shape to an octahedral form (bounded by (111)) when the (100) planes grow more quickly than the (111) planes (a). Often, impurities change the growth behaviour of specific planes and this results in the appearance of different growth forms for the same crystal structure. If the (110) planes are the slowest-growing, this will lead to a rhombohedral dodecahedron (b). The slowest-growing planes (usually of low-index type) always dictate the growth habit of the crystal. The resultant minimum growth rate form is not the same as the equilibrium (non-growing) form, which is governed by minimisation of the total surface energy.

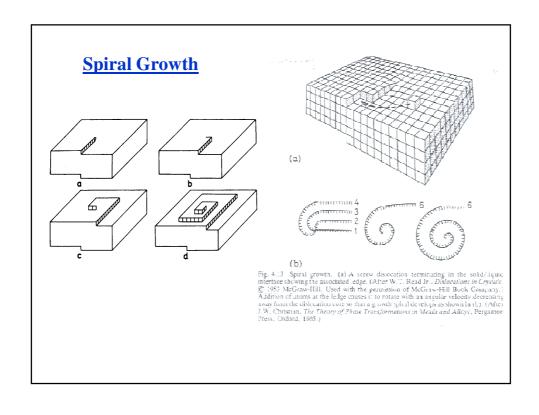


A sapphire nano-wire growth

Sapphire nano-wires produced using a vapour-liquid-solid (VLS) nano-wire growth technique directly on a TEM microscope 'hot stage'.







Spiral Growth



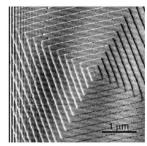
Figure 6.5. A circular spiral on a silicon carbide crystal. (Courte Westinghouse Corporation)



 $\label{eq:Figure 21} Figure \ 21 \ Phase \ contrast \ micrograph \ of \ a \ hexagonal \ spiral \ growth \ pattern \ on \ a \ SiC \ crystal. \ The step height is 165 Å. (A. R. Verma.)$



Figure 6.6. An elliptical spiral on the (100) face of an ammonium dihydrogen phosphate crystal growing in aqueous solution (Davey and Mullin, 1974)



 ${\it BaSO}_4 \ growth \ spiral \ imaged, \ during \ precipitation, \\ with \ AFM. \ Bright \ and \ dark \ lines \ are \ elementary \\ step \ edges, \ each \ only \ 0.75 \ nm \ high.$

Growth on Twin Boundries

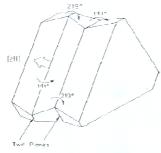


FIGURE 9-24
Germanium crystal with two twin planes has six favored reentrant sites 60° apart.
(From Hamilton and Seidensticker, 4°)

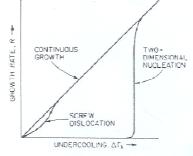


FIGURE 9-14 Growth rate versus interface undercooling according to the three classical laws.

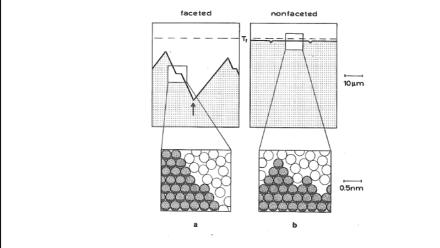
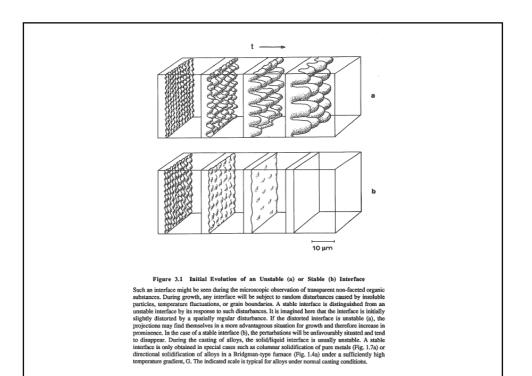


Figure 2.8 Form of Faceted (a) and Non-Faceted (b) Interfaces

A transparent organic substance, when observed under the microscope during directional solidification (upwards growth, bottom cool, top hot), can exhibit either of the growth forms shown in the upper diagrams. It is important to note that, during growth, a faceted interface (a) is jagged and faceted at the microscopic scale (upper diagram), but smooth at the atomic scale (lower diagram), on the other hand, a non-faceted interface (b) can be microscopically flat with some slight depressions due to grain boundaries (upper diagram), while at the atomic scale it is rough and uneven (lower diagram). This roughness causes the attachment of atoms to be easy and largely independent of the crystal orientation. Note also that the interface of a non-faceted material will grow at a temperature which is close to the melting point, T_p, while the interface of a faceted material might have a very high-local undercooling. Such a point (arrow) is a re-entrant corner (Fig. 2.10), and is associated with an increased number of nearest neighbours. Thus, growth will tend to spread from here.



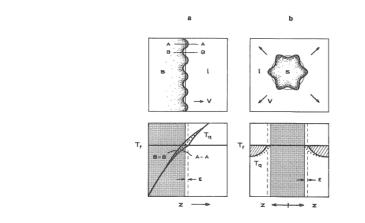


Figure 3.2 Columnar and Equiaxed Solidification of a Pure Substance

Figure 3.2 Columnar and Equiaxed Solidification of a Pure Substance

In a pure substance, stability depends on the direction of heat flow. In directional solidification, as in the columnar zone of a casting, the liquid temperature always increases ahead of the interface (a). Therefore, the heat flow direction is opposite to that of solidification. When a perturbation of amplitude, e, forms at an initially smooth interface, the temperature gradient in the liquid increases while the gradient in the solid decreases (compare full and dotted lines along section, A-A). Since the heat flux is proportional to the gradient, more heat then flows into the tip of the perturbation and less flows out of it into the solid. As a result, the perturbation melts back and the planar interface is stabilised. In equiaxed solidification, the opposite situation is found (b). Here, the free crystals grow into an undercooled melt (cross-hatched region) and the latent heat produced during growth also flows down the negative temperature gradient in the liquid. A perturbation which forms on the sphere will make this gradient steeper (full line compared to the dotted line) and permit the tip to reject more heat. As a result, the local growth rate is increased and the interface is always morphologically unstable.

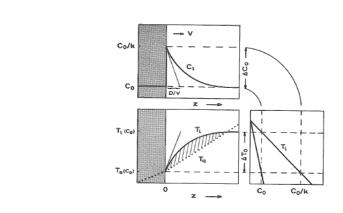
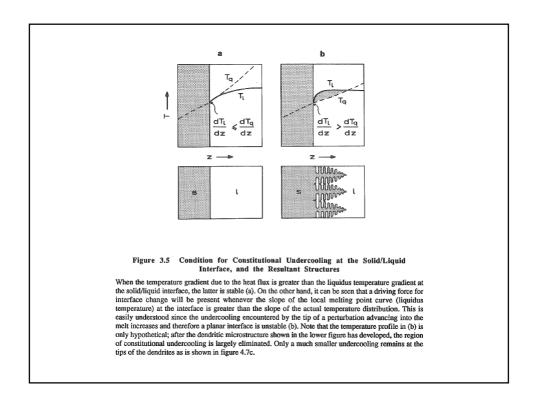
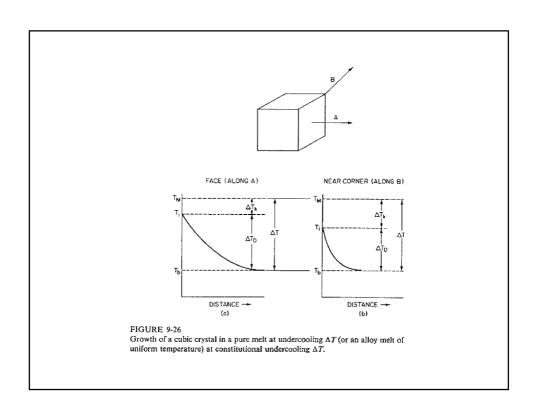


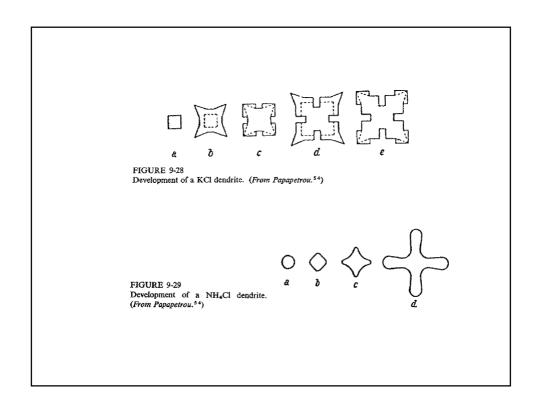
Figure 3.4 Constitutional Undercooling in Alloys

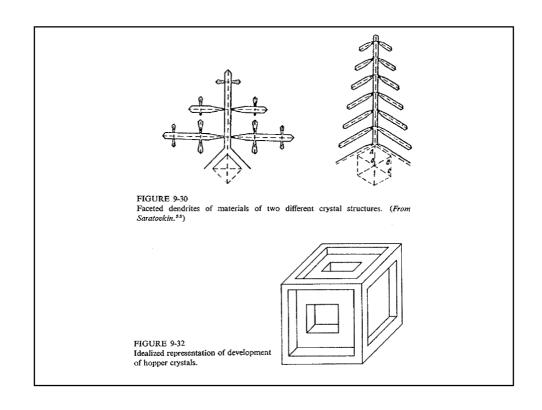
Figure 3.4 Constitutional Undercooling in Alloys

The steady-state diffusion boundary layer, shown in figure 3.3, is reproduced here (upper diagram) for a given growth rate. As the liquid concentration, C_L decreases with distance, z, the liquids temperature, T_L (i.e. the melting point), of the alloy will increase as indicated by the phase diagram. This means that if small volumes of liquid at various distances ahead of the solid/liquid interface were extracted by some means and solidified, their equilibrium frecing points would vary with position in the manner described by the heavy curve in the lower left-hand diagram. However, each volume element finds itself at a temperature, T_{C_L} which is imposed by the temperature gradient arising from the heat flow occurring in the casting. Since, at the solid/liquid interface (z=0), T_Q must be less than or equal to T_S in order to drive the atomic addition mechanism, there may exist a volume of liquid which is undercooled when the gradient of T_L . This (cross-hatched) region is called the zone of constitutional undercooling. There exists a driving force for the development of perturbations in this volume as in the cross-hatched region of figure 3.2b.









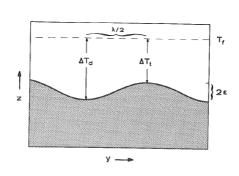


Figure 3.6 Interface Perturbations at a Solid/Liquid Interface

The existence of a zone of constitutional undercooling implies that a driving force for a change in the morphology is available, but gives no indication of the scale of the morphology which will appear. Experimental observations show that the initial form of the new morphology is periodic and may be approximated by a sinusoidal curve. Perturbation analysis permits the calculation of the wavelength of the instabilities which develop. The result is of great importance in the theory of dendrite growth.

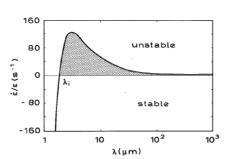


Figure 3.7 Rate of Development of a Perturbation at a Constitutionally Undercooled Interface

Here the parameter, $\dot{\epsilon}/\epsilon$, describes the relative rate of development of the amplitude of a small sinusoidal perturbation in the case of a specific alloy (Al-2wr%Cu) under given growth conditions (V=0.1 mm/s, G=10 K/mm). At very short wavelengths, the value of this parameter is negative due to curvature damping and the perturbation will tend to disappear (Fig. 3.1b). At wavelengths greater than λ_i and above, the sinusoidal shape will become more accentuated (instability-figure 3.1a). The wavelength having the highest rate of development is likely to become dominant. The reason for the tendency to stability at high λ -values is the difficulty of diffusional mass transfer over large distances. When the interface is completely stable, the curve will remain below the $\dot{\epsilon}/\epsilon=0$ line for all wavelengths. This implies the disappearance of perturbations having any of these wavelengths (appendix 7).

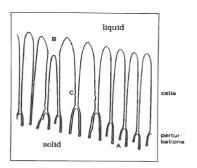


Figure 4.3 Breakdown of a Plane Solid/Liquid Interface to Give Cells

Figure 4.3 Breakdown of a Plane SolidAl.dquid Interface to Give Cells
The development of perturbations at the constitutionally undercooled solid/liquid interface (lower part of
figure) is only a transient phenomenon. The tips of the perturbations can readily reject solute while the
depressed parts of the interface accumulate solute and advance much more slowly. The initial
wavelength is too small for further rapid growth to occur, and the final result is the formation of a
cellular structure. Note that the wavelength has approximately doubled between the initial perturbation
and the final cells. Also, the spacing between the cells is not constant. The initial cellular morphology
can adjust itself to give a more optimum growth form via the cessation of growth of some cells (B) in
order to decrease their number, or by the division of cells in order to increase the number present. The
division of cells is not shown here, but it resembles the change at point A, with two branches
continuing to grow. Furthermore, the larger centre cells (C) have slightly perturbed surfaces and this
suggests that, in the intercellular liquid, some driving force remains for further morphological change
which might possibly lead to dendrite formation.

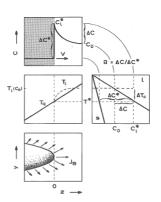


Figure 4.8 Solute Rejection at the Tip of an Isolated Dendrite

Figure 4.8 Solute Rejection at the Tip of an Isolated Dendrite During directional solidification, where the isotherms move due to the imposed heat flux, a needle-like crystal can grow more quickly than a flat interface due to the more efficient solute redistribution: Tautoms rejected at the interface of a thin needle can diffuse outwards into a large volume of liquid. Thus, the solutal diffusion boundary layer, δ_c , of the needle is smaller than that of a planar interface. Also, because the interface is not planar, the solid formed does not have the same composition as the original liquid (as it does in the case of steady-state plane-front growth – Fig. 3.4). When a positive gradient is imposed, as in directional solidification, heat is extracted through the solid. If, furthermore, thermal diffusion is rapid (as in metals) the form of the isotherms will be affected only slightly by the interface morphology. Thus, in the case of directionally solidifying dendrites, solute diffusion alone will be the limiting factor. The growth temperature, T, of the ip will define a solute undercooling, ΛT_c , or, via the phase diagram, the degree of superstantation, $\Omega = \Delta C/\Delta C^*$. The determination of Ω as a function of the other parameters requires the solution of the differential equation which describes the solute distribution. The simplest solution is obtained when the tip morphology is supposed to be hemispherical. Instead, the real form of the dendrite tip is closely represented by a paraboloid of revolution.

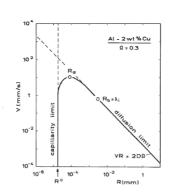
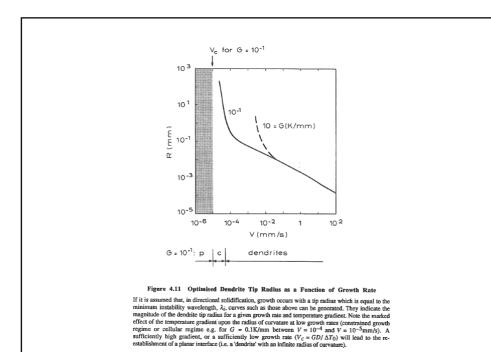
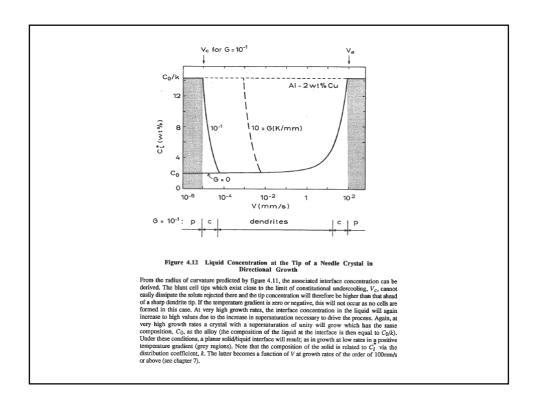
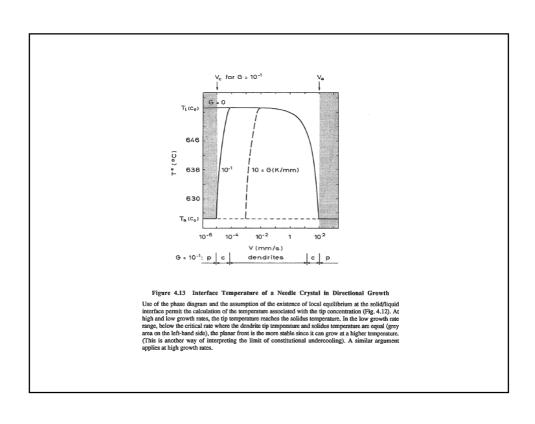


Figure 4.9 Unoptimised Growth Rate of a Hemispherical Needle for Ω = Constant

Figure 4.9 Unoprimised Growth Rate of a Hemispherical Needle for Ω = Constant For a hemispherical needle crystal, the solution of the diffusion equation shows that the supersaturation, Ω , is equal to the ratio of the tip radius to the characteristic diffusion length. This dimensionless ratio is known as the Péclet number, P_c (= RV/2D). For a given supersaturation, the product, RV, is therefore constant and means that either a dendritie with a small radius will grow rapidly or one with a large radius will grow slowly (diagonal line). At small R-values, the diffusion limit is cut by the capillarity limit. The minimum radius, R^0 , is given by the critical radius of nucleation, P^c (table 2.1). A maximum value of V therefore exists. Because it was reasoned that the fastest-growing dendrites would dominate steady-state growth, it was previously assumed that the radius chosen by the system would be the one which gave the highest growth rate (extremum value, $R = R_0$). However, experiment indicates that the radius of curvature of the dendrite is approximately equal to the lowest wavelength perturbation of the tip, which is close to λ_i (Fig. 3.7). This is referred to as growth at the limit of stability ($R = R_2$).







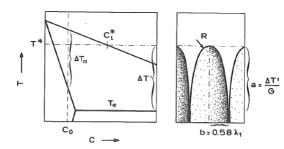


Figure 4.14 Estimation of the Primary Spacing in Directional Solidification

In practical applications, the dendrite tip radius is not as important a parameter as the primary spacing since it is very difficult to measure it directly. However, the tip radius has some influence on the primary spacing. In order to estimate the primary spacing, the dendrites are imagined to be elliptical in shape. The length of the major half-axis, a, of the ellipse is equal to $\Delta T'/G$. Here, $\Delta T'$ is the difference between the tip temperature and the melting point of the last interdendritic liquid. The primary spacing, λ_1 , which is proportional to the minor half-axis, b, can be determined from simple geometrical considerations. The factor, 0.58, arises from the assumption that the dendrite trunk arrangement is close-packed hexagonal.

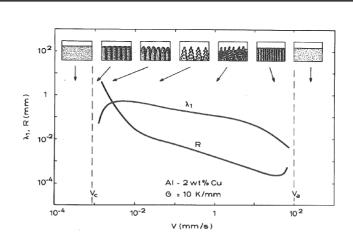
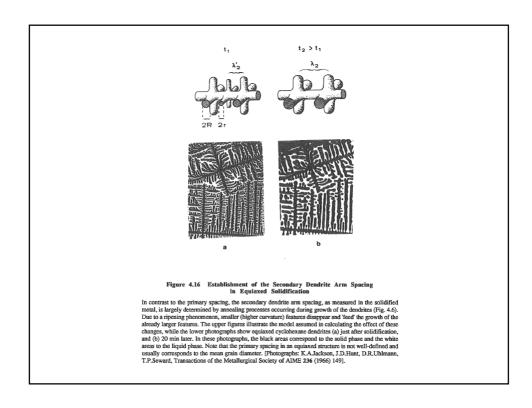
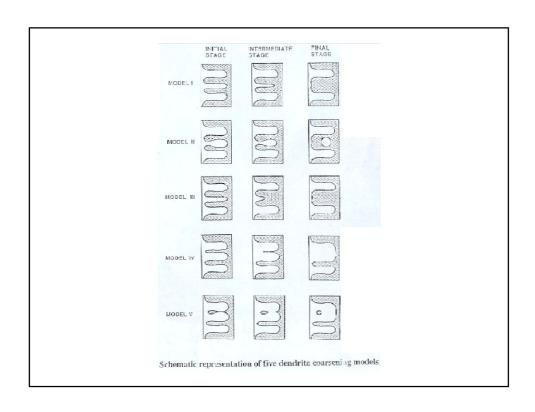
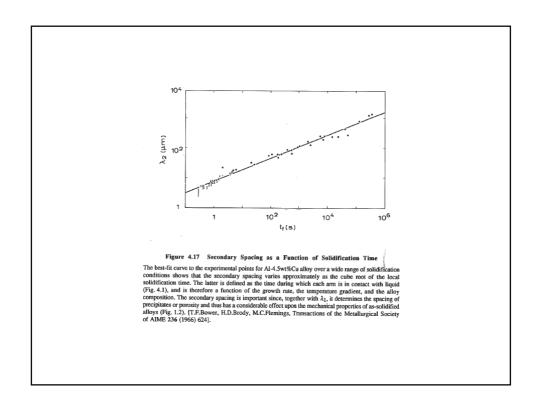


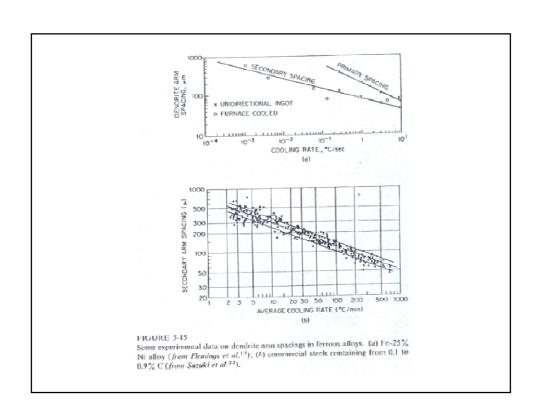
Figure 4.15 Morphology, Tip Radius, and Spacing of Cells and Dendrites

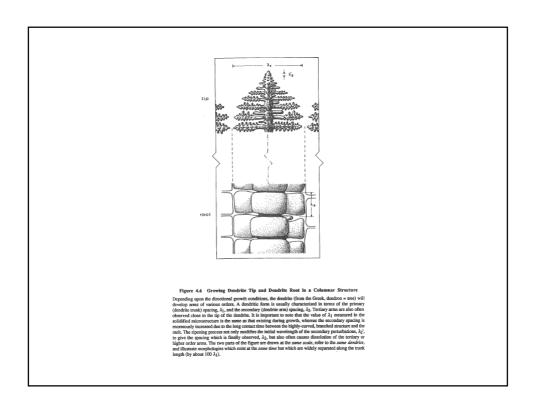
According to the dendrite model, the tip radius decreases from very large values at the limit of constitutional undercooling, V_c , to small values at high growth rates (as in figure 4.11). Over the range of dendritic growth, the primary spacing decreases approximately as the square-root of R (equation 4.18). The corresponding interface structures are also shown and vary from planar at growth rates less than V_c to cells and to dendrites which become finer and finer until they give rise to cellular structures again when close to the limit of absolute stability. At $V > V_a$, cell solidification structures disappear and again give a planar interface. (For more details on rapid V_a growth, see chapter 7).

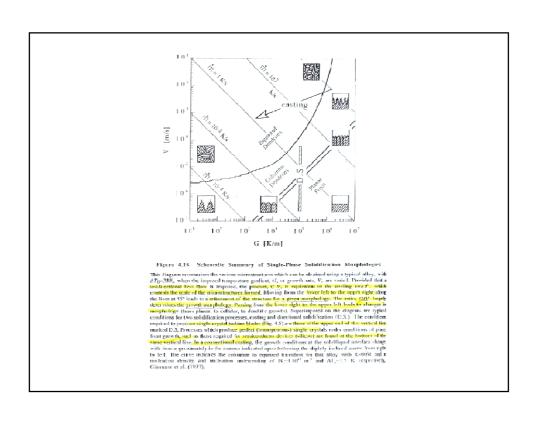












During solidification, the solid/ liquid interface rejects solute into the liquid (we consider here the frequent case when the solubility of the solute element in the solid is smaller than in the liquid). This will always lead to concentration variations in the solidified alloy, known as micro-segregation. The understanding of this phenomenon is the key to interpreting the influence of solidification on the mechanical properties of cast products. Modeling is greatly facilitated by distinguishing between important factors and non-important ones.







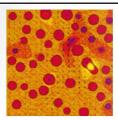


Figure b) Transversal representation of growing dendrites (red line in Figure a).

← Case

An Al-2%Cu alloy is solidifying uni-directionally at a constant velocity V_t. The temperature gradient C is imposed by the experimental configuration and we consider for simplicity that there is no flow. The primary dendrite arm spacing is defined as A.

1 for illustration:

Number	Symbol	Value	Unit	Name
1	V _L	0.1	mm/s	Isotherm speed
2	G	1000	K/m	Thermal gradient
3	k	0.14	-	Equilibrium distribution coefficient
4	m	-2.6	K/wt%	Liquidus slope
5	T,	660	°C	Melting point of pure Al
6	T _{eur}	574	°C	Eutectic temperature
7	C _o	2	wt%	Alloy concentration
8	Cnr	33.1	wt%	Eutectic concentration
9	λ	500	µ m	Primary dendrite arm spacing
10	D,	3 · 10 9	m²/s	Diffusion coefficient in liquid
11	D,	3 · 10 · 12	m²/s	Diffusion coefficient in solid
12	а	3.7 · 10 5	m²/s	Thermal diffusivity

Table 1:

Values 1-2, 9 are given by the experiment, they should be measured.

Values 3-6, 8 are given by the phase diagram of the Al-Cu system.

Value 7 is an input of the problem.

Results

1) Liquidus temperature, $T_{\rm L}$

The liquidus temperature can be calculated as follow:

 $T_L = T_o + m \cdot C_o = 654.8 \, ^{\circ}C$

2) Mushy zone length, L_M

The mushy zone length can be calculated as follow:

 $L_{M} = (T_{L} - T_{EUT}) / G = 0.0808 [m]$ = 8.08 [cm], not so small!

3) Local solidification time, t_s

The local solidification time can be calculated as follow:

 $t_s = L_M / V_L = 808 [s] = 13.5 minutes$

4) Mean transversal speed of the solid/liquid interface in Figure b), $\mathbf{V}_{\scriptscriptstyle T}$

The mean speed of the s/l interface in view b) can be calculated as follow:

 $\begin{array}{l} V_{_{T}} = ({1\!\! /}2) \; / \; t_{_{S}} = 3.1 \; \cdot 10^{.7} \; [m/s] \\ = 0.31 \; [\mu m/s] << V_{_{L}} \end{array}$

The transversal growth speed is much smaller than the longitudinal growth rate.

 $\begin{array}{l} L_{_{THERMAL}} = \text{tt} / \ V_{_{T}} = 119.7 \ [m] >> \text{\lambda} \\ L_{_{SOLUTAL}} = D_{_{L}} / \ V_{_{T}} = 9.7 \ [mm] >> \text{\lambda} \end{array}$

This means that the temperature in the liquid can be considered as uniform as well as the concentration (complete mixing). Note that the thermal diffusion length is 10'000 larger than the solutal one.

6) Estimation of the thermal and solutal diffusion lengths ahead of the primary dendrite tips

The solutal gradient ahead of the primary dendrite tips cannot be neglected.

7) Estimation of the characteristic solutal diffusion times in the liquid and solid on the scale of dendrite arm spacing (Figure b))

 $\begin{array}{l} t_{_{\rm IIQUID}} = (\pmb{\Lambda}/2)^2 \, / \, \, D_{_L} = 20.8 \, \, [s] << t_{_S} \\ t_{_{_{SCLID}}} = (\pmb{\Lambda}/2)^2 \, / \, \, D_{_S} = 2 \cdot 10^5 \, \, [s] >> t_{_S} \end{array}$

This means that there is enough time to smooth concentrations profiles in the liquid while this is not the case in the solid, i.e. a gradient in the solid will be present after solidification.

8) Estimation of the characteristic solutal diffusion time in the liquid over the length of the mush

 $t_{\text{LIQUID}} = (L_{\text{M}})^2 / D_{\text{L}} = 2.2 \cdot 10^6 [s] >> t_{\text{S}}$

This means that solutal diffusion in the liquid parallel to dendrites can be neglected because the characteristic time is much greater that the solidification time

Conclusion

Knowing the importance of the these "orders of magnitude" influences on solidification can help us to distinguish between important factors and less important factors. These can then help us develop more simplified, but realistic, computer models of solidification phenomena while saving a lot of calculation time.